NCE P-Channel Super Trench Power MOSFET

Description

The NCEP40P80G uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

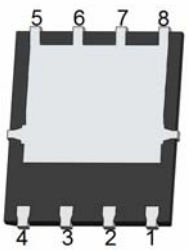
General Features

- V_{DS} =-40V,I_D =-80A
  $R_{DS(ON)}$=6.3mΩ (typical) @ V_{GS}=-10V
  $R_{DS(ON)}$=9.0mΩ (typical) @ V_{GS}=-4.5V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating

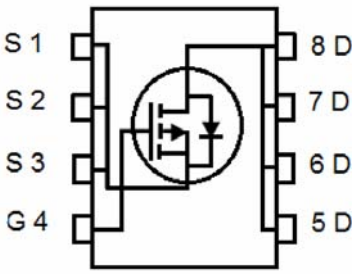
100% UIS TESTED!
100% ΔVds TESTED!

DFN 5X6

Top View



Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP40P80G	NCEP40P80G	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D(T_C=25℃)	-80	A
Drain Current-Continuous(T_C=100℃)	I_D (T_C=100℃)	-56	A
Drain Current-Continuous (T_A=25℃)	I_D(T_A=25℃)	-12.8	A
Pulsed Drain Current	I_{DM}	-320	A
Maximum Power Dissipation(T_C=25℃)	P_D(T_C=25℃)	75	W
Maximum Power Dissipation(T_A=25℃)	P_D(T_A=25℃)	2.3	W
Pulsed Drain Current	I_{DM}	-320	A
Derating factor		0.6	W/℃
Single pulse avalanche energy (Note 3)	E_{AS}	500	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	1.67	℃/W
Thermal Resistance,Junction-to-Ambient(Note 1)	$R_{\theta JA}$	55	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-40		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-40V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.1	-1.6	-2.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-20A	-	6.3	7.5	mΩ
		V_{GS}=-4.5V, I_D=-20A	-	9.0	12.0	mΩ
Gate resistance	R_G		-	2.0	-	Ω
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-20A	-	30	-	S
Dynamic Characteristics (Note2)						
Input Capacitance	C_{lss}	V_{DS}=-20V,V_{GS}=0V, F=1.0MHz	-	3700	-	PF
Output Capacitance	C_{oss}		-	880	-	PF
Reverse Transfer Capacitance	C_{rss}		-	20	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-20V,I_D=-20A V_{GS}=-10V,R_G=1.6Ω	-	10.5	-	nS
Turn-on Rise Time	t_r		-	4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	35	-	nS
Turn-Off Fall Time	t_f		-	5	-	nS
Total Gate Charge	Q_g	V_{DS}=-20V,I_D=-20A, V_{GS}=-10V	-	57	-	nC
Gate-Source Charge	Q_{gs}		-	9.8		nC
Gate-Drain Charge	Q_{gd}		-	7.3		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=-20A	-		-1.2	V
Diode Forward Current	I_S		-	-	-80	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F =-20A di/dt = 100A/μs	-		24	nS
Reverse Recovery Charge	Qrr		-		68	nC

Notes:

1. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C.
2. Guaranteed by design, not subject to production
3. EAS condition : Tj=25℃,V_{DD}=-20V,V_G=-10V,L=0.5mH,Rg=25Ω

Typical Electrical and Thermal Characteristics

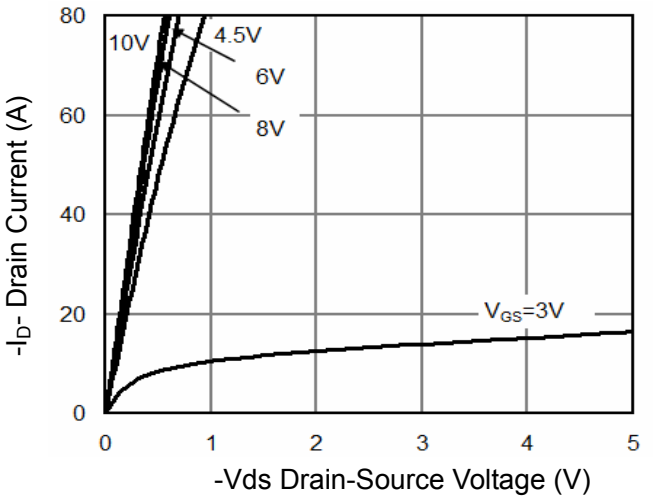


Figure 1 Output Characteristics

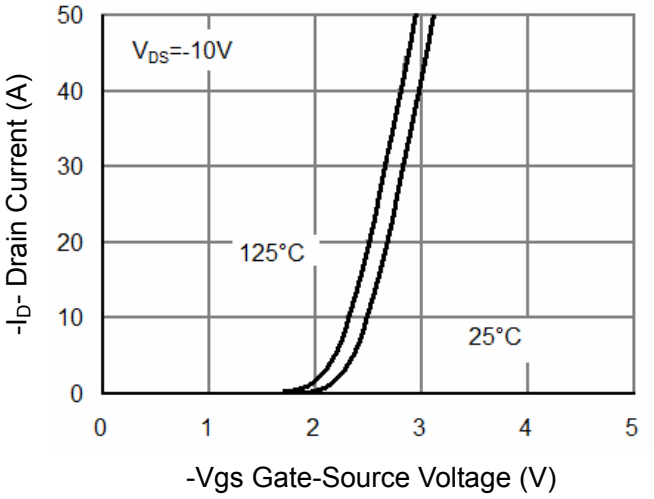


Figure 2 Transfer Characteristics

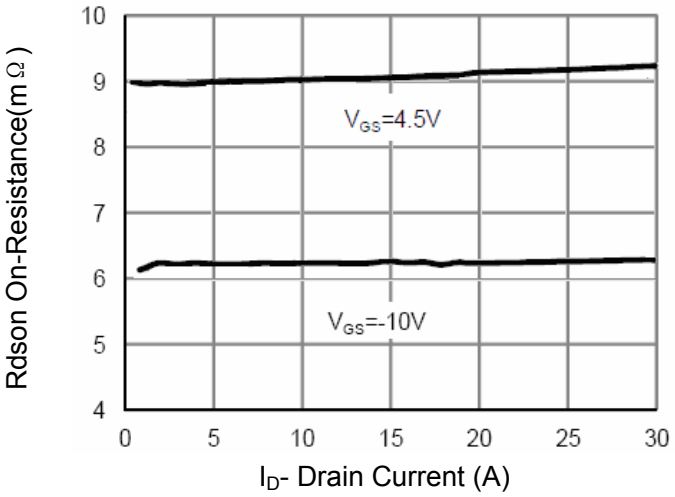


Figure 3 Rdson- Drain Current

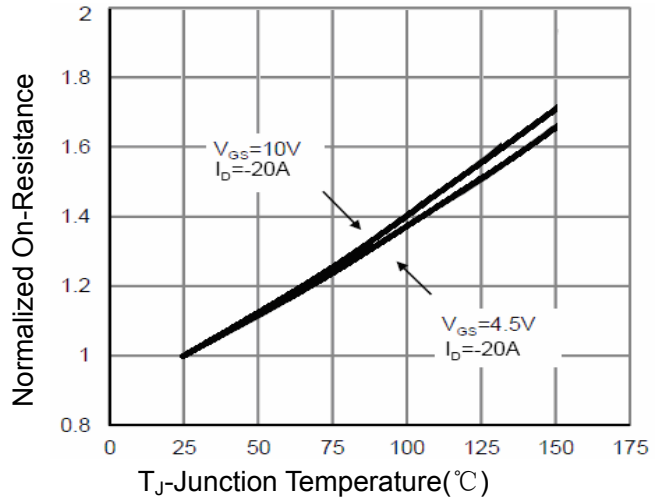


Figure 4 Rdson-JunctionTemperature

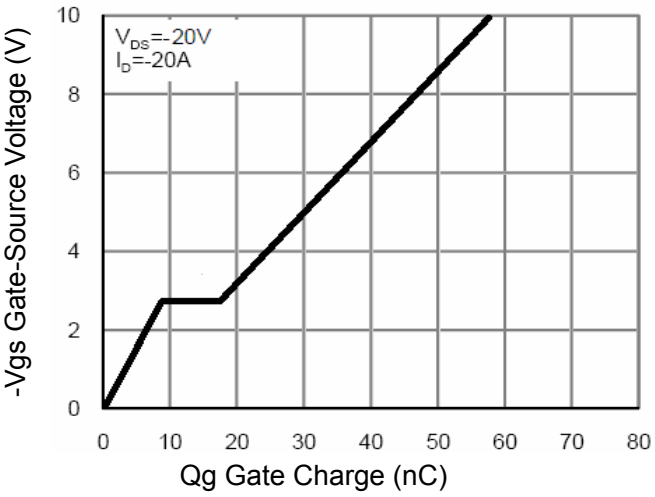


Figure 5 Gate Charge

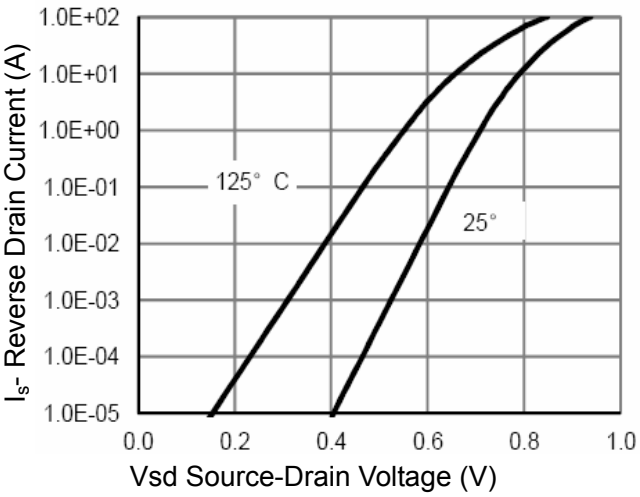


Figure 6 Source- Drain Diode Forward

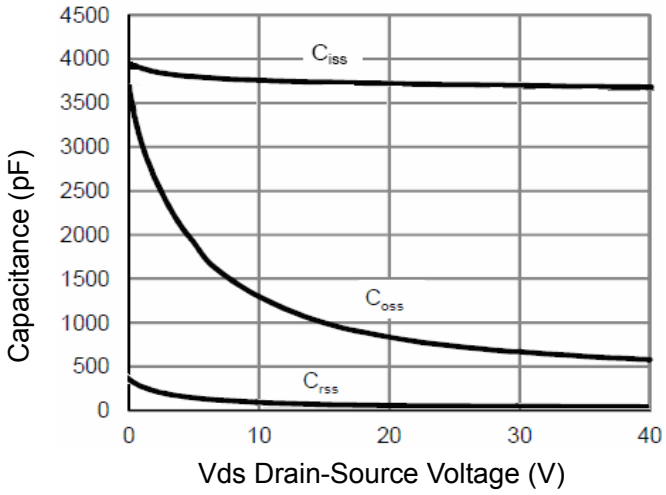


Figure 7 Capacitance vs Vds

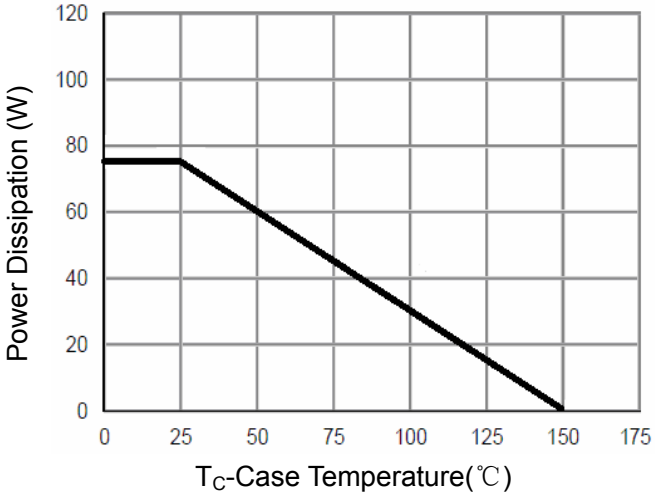


Figure 9 Power De-rating

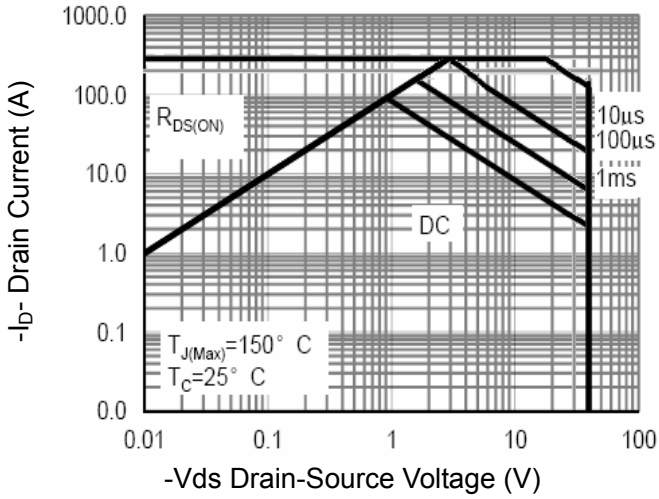


Figure 8 Safe Operation Area

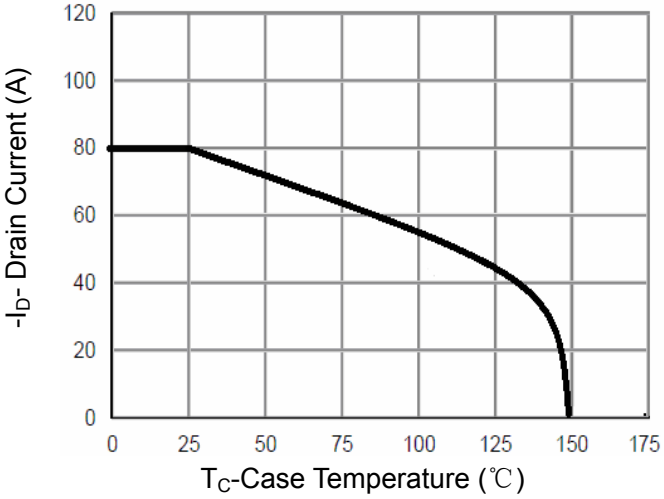


Figure 10 Current De-rating

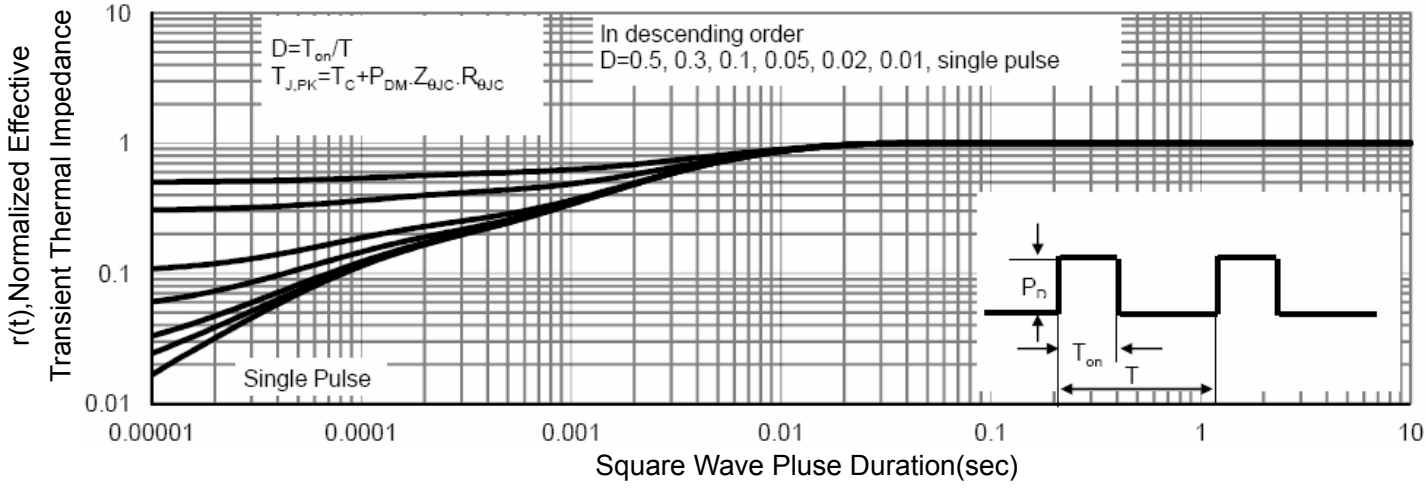
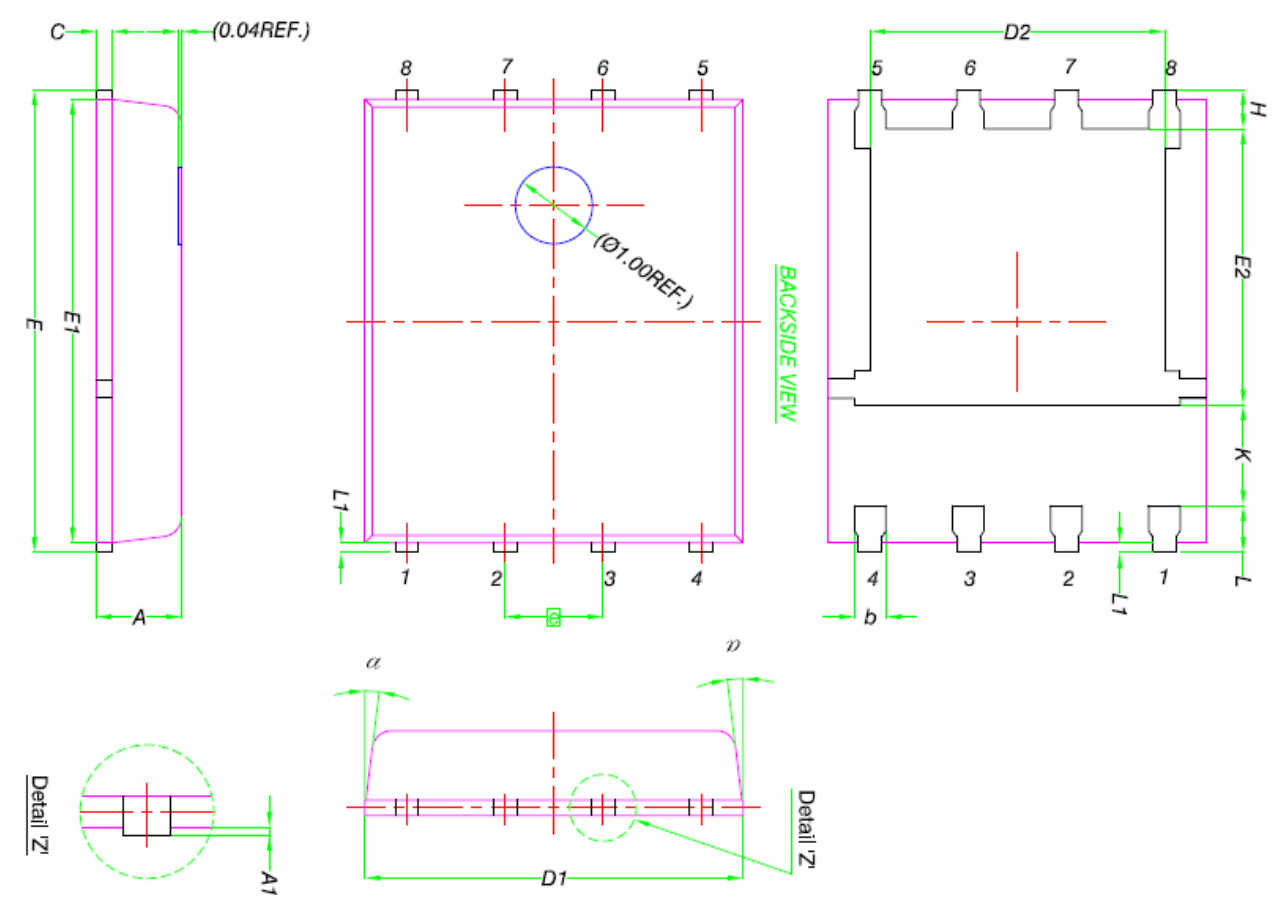
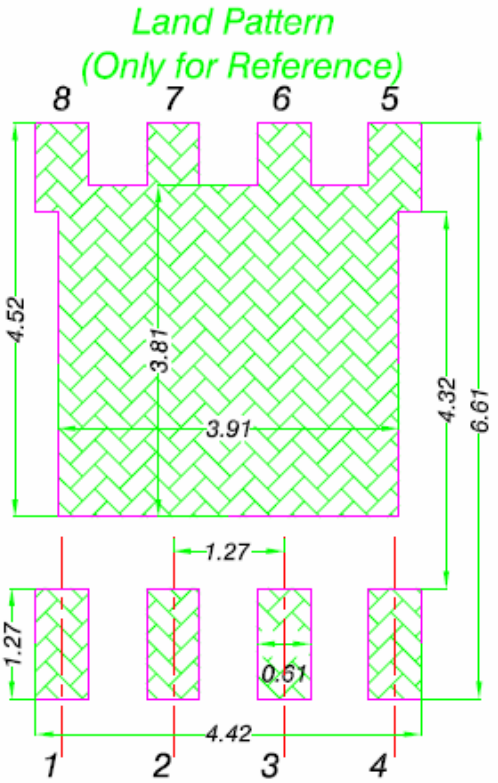


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°



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